**Publisher's Note: Strain Engineering of the Band Gap of HgTe Quantum Wells
Using Superlattice Virtual Substrates
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This Letter was published online on 19 August 2016 with a typographical error on page 4. On page 4, left-hand column, the thirteenth line should read as “at higher fields. The n -type carrier density at the onset of two carrier conductance (black arrow) is $n_e^* = 5.5 \times 10^{10} \text{ cm}^{-2}$ ”. The Letter has been corrected as of 11 August 2017. The text is incorrect in the printed version of the journal.